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Supporting Information

Unlocking high capacitive energy-density in Sm-doped Pb(Mg_{1/3}Nb_{2/3})O₃–PbTiO₃ thin films *via* strain and domain engineering

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1. Chemical compositions of Sm-PMN-30PT thin film



Fig. S1. Chemical compositions of Sm-PMN-30PT thin film. Bright-field TEM image showing the heterostructure Sm-PMN-30PT/SRO/TSO and EDS elemental mappings of Sm, Pb, Mg, Nb, Ti, Sr, Ru, Tb, and Sc elements.

2. Lattice strain and lattice parameters of Sm-PMN-30PT thin film

Table S1: Evaluation of lattice strain (in percentage) and lattice parameters based on GPA analysis ofHAADF-STEM images shown in Figure S1.

		a		С		
		Strain	Dimension	Strain	Dimension	
		(%)	(nm)	(%)	(nm)	
Fig. S1a	TSO substrate	Reference	0.396	Reference	0.396	
	SRO electrode	-0.01	0.396	-1.5	0.390	
Fig. S1b	SRO electrode	Reference	0.396	Reference	0.390	
	Sm-PMN-30PT layer	+1.5 (gradual)	0.402	+3.4	0.403	

3. Phases and nanodomain structures of Sm-PMN-30PT thin film



Fig. S2. Phases and nanodomain structures of Sm-PMN-30PT thin film. (a) Atomic resolution HAADF-STEM images of a 35 × 35 unit-cell area viewed along the $[100]_{pc}$ zone axis. The larger spots correspond to the A-site columns and smaller spots to the B-site columns. The inset shows the B-site displacements (δ_B) from the center of four neighboring A-site atoms of the perovskite unit cell $(\delta_{A-A}$ is the distance between A-site atoms). (b) Vector map of B-site displacements away from the center of the A-site perovskite sublattice. Arrows mark the direction and magnitude (arrow length) of the displacements, and the contours additionally mark their magnitude.



Fig. S3. Polar plot of the B-site atom displacements. The arrow indicates the average magnitude andangleofthedisplacement.

Dielectric films	<i>E_{max}</i> (MV cm ⁻¹)	<i>W_{rec}</i> (J cm ⁻³)	η (%)	<i>W_{rec}/E_{max}</i> (J MV ⁻¹ cm ⁻²)	<i>Q_F</i> (kJ cm ⁻³)	Ref.
Sm-PMN-30PT	4	116.1	73	30.0	430	This work
30 mol% Sm-doped 0.3BiFeO ₃ -0.7BaTiO ₃	5.2	152	77	29.2	660.9	[1]
$(0.7Na_{0.5}Bi_{0.5}TiO_3-0.3SrTiO_3)/(0.6SrTiO_3-0.4Na_{0.5}Bi_{0.5}TiO_3)$	2.61	60	51	23.0	122.4	[2]
0.25BiFeO ₃ -0.30BaTiO ₃ -0.45SrTiO ₃	4.9	112	80	22.9	560.0	[3]
$0.68Pb(Mg_{1/3}Nb_{2/3})O_3-0.32PbTiO_3$	5.92	133.3	75	22.5	533.2	[4]
(0.4BiFeO ₃ -0.6SrTiO ₃)/Ba _{0.5} Sr _{0.5} TiO ₃	4.76	98	80	20.6	490.0	[5]
0.30BiFeO ₃ -0.35BaTiO ₃ -0.35SrTiO ₃	4	79	78	19.8	359.1	[6]
La-doped 0.9Na _{0.5} Bi _{0.5} TiO ₃ -0.1BiFeO ₃	2.7	52.4	60.3	19.4	132.0	[7]
0.9Na _{0.5} Bi _{0.5} TiO ₃ -0.1BiFeO ₃	2	38.5	52	19.3	80.2	[8]
$Pb_{0.9}La_{0.1}(Zr_{0.52}Ti_{0.48})O_3$	3.6	68.2	80.4	18.9	348.0	[9]
Na _{0.5} Bi _{0.5} TiO ₃	1.25	23.3	61.6	18.6	60.7	[10]
$0.4BiFeO_3$ - $0.6SrTiO_3$	3.85	70.3	70	18.3	234.3	[11]
$Pb_{0.9}La_{0.1}(Zr_{0.52}Ti_{0.48})O_3/Pb(Zr_{0.52}Ti_{0.48})_{0.99}Nb_{0.01}O_3$	2.45	43.5	84.1	17.8	273.6	[12]
$0.65Pb(Mg_{1/3}Nb_{2/3})O_3-0.35PbTiO_3$	2	35	70	17.5	116.7	[13]
$0.88Ba_{0.55}Sr_{0.45}TiO_3\text{-}0.12BiMg_{2/3}Nb_{1/3}O_3$	5	86	73	17.2	318.5	[14]
0.25BiFeO ₃ -0.75SrTiO ₃	4.46	70	68	15.7	218.8	[11]
Mn-doped Pb _{0.97} La _{0.02} (Zr _{0.905} Sn _{0.015} Ti _{0.08})O ₃	2	31.2	58	15.6	74.3	[15]
0.5 mol% Mn-doped 0.4BiFeO ₃ -0.6SrTiO ₃	3.6	51	64	14.2	141.7	[16]
$Pb_{0.9}La_{0.1}Zr_{0.52}Ti_{0.48}O_3$	3	40.9	80.2	13.6	206.6	[17]
$0.6PbTiO_3$ - $0.4Bi(Mg_{0.5}Zr_{0.5})O_3$	2.6	32.3	51.4	12.4	66.5	[18]
$Ba_{0.7}Ca_{0.3}TiO_3/BaZr_{0.2}Ti_{0.8}O_3$	4.5	52.4	72.3	11.6	189.2	[19]
$BaZr_{0.35}Ti_{0.65}O_3$	8.7	100.8	78	11.6	458.2	[20]
Sm-doped BaZr _{0.2} Ti _{0.8} O ₃	3.68	40.42	85	11.0	270.0	[21]
0.01 mol% Mn-doped 0.55Na _{0.5} Bi _{0.5} TiO ₃ -0.45Sr _{0.2} Bi _{0.7} TiO ₃	2.86	30.5	65	10.7	87.1	[22]

Table S1. Comparison of the energy storage parameters (W_{rec} , η , E_{max} and W_{rec}/E_{max}) of Sm-PMN-30PT and other relaxor ferroelectric thin films reported in literature.

$BaZr_{0.2}Ti_{0.8}O_3$	3	30.4	81.7 10.1	166.1	[23]

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